



## 桥式整流器 Bridge Rectifier

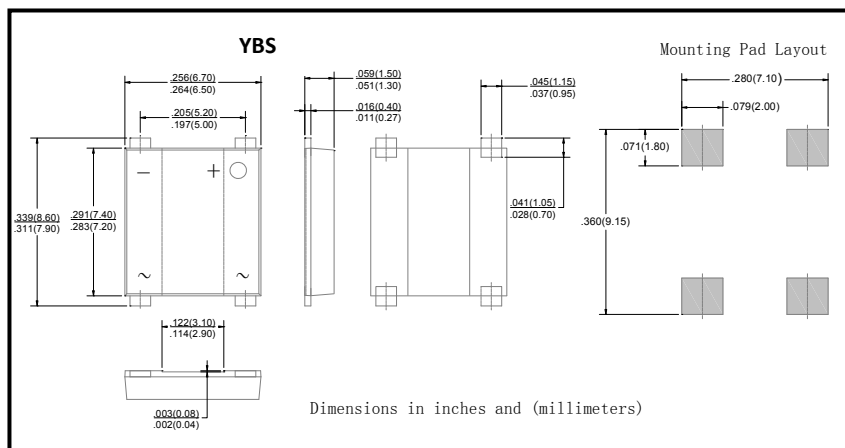
## ■特征 Features

- $I_o$  2.2A
- $V_{RRM}$  50-1000V
- 玻璃钝化芯片  
Glass passivated chip
- 耐正向浪涌电流能力高  
High surge forward current capability

## ■用途 Applications

- 作一般电源单相桥式整流用  
General purpose 1 phase Bridge rectifier applications

## ■外形尺寸 Outline Dimensions and Mark



## ■极限值（绝对最大额定值）

## Limiting Values (Absolute Maximum Rating)

| 参数名称<br>Item                                        | 符号<br>Symbol | 单位<br>Unit           | 条件<br>Conditions                                                                                                                                         | YBS22      |     |     |     |     |     |      |
|-----------------------------------------------------|--------------|----------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------|------------|-----|-----|-----|-----|-----|------|
|                                                     |              |                      |                                                                                                                                                          | 005        | 01  | 02  | 04  | 06  | 08  | 10   |
| 反向重复峰值电压<br>Repetitive Peak Reverse Voltage         | $V_{RRM}$    | V                    |                                                                                                                                                          | 50         | 100 | 200 | 400 | 600 | 800 | 1000 |
| 平均整流输出电流<br>Average Rectified Output Current        | $I_o$        | A                    | 60Hz正弦波, 电阻负载, $T_c=110^{\circ}\text{C}$<br>60Hz sine wave, R-load, $T_c=110^{\circ}\text{C}$                                                            | 2.2        |     |     |     |     |     |      |
| 正向（不重复）浪涌电流<br>Surge(Non-repetitive)Forward Current | $I_{FSM}$    | A                    | 60Hz正弦波, 一个周期, $T_j=25^{\circ}\text{C}$<br>60Hz sine wave, 1 cycle, $T_j=25^{\circ}\text{C}$                                                             | 90         |     |     |     |     |     |      |
| 正向浪涌电流的平方对电流浪涌持续时间的积分值<br>Current Squared Time      | $I^2t$       | $\text{A}^2\text{S}$ | $1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^{\circ}\text{C}$ , 单个二极管<br>$1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^{\circ}\text{C}$ , Rating of per diode | 33         |     |     |     |     |     |      |
| 存储温度<br>Storage Temperature                         | $T_{stg}$    | $^{\circ}\text{C}$   |                                                                                                                                                          | -55 ~ +150 |     |     |     |     |     |      |
| 结温<br>Junction Temperature                          | $T_j$        | $^{\circ}\text{C}$   |                                                                                                                                                          | -55 ~ +150 |     |     |     |     |     |      |

■电特性（ $T_a=25^{\circ}\text{C}$  除非另有规定）Electrical Characteristics ( $T_a=25^{\circ}\text{C}$  Unless otherwise specified)

| 参数名称<br>Item                   | 符号<br>Symbol     | 单位<br>Unit                  | 测试条件<br>Test Condition                                                                                  | 最大值<br>Max                       |
|--------------------------------|------------------|-----------------------------|---------------------------------------------------------------------------------------------------------|----------------------------------|
| 正向峰值电压<br>Peak Forward Voltage | $V_{FM}$         | V                           | $I_{FM}=1.1\text{A}$ , 脉冲测试, 单个二极管的额定值<br>$I_{FM}=1.1\text{A}$ , Pulse measurement, Rating of per diode | 1.02                             |
|                                |                  |                             | $I_{FM}=2.2\text{A}$ , 脉冲测试, 单个二极管的额定值<br>$I_{FM}=2.2\text{A}$ , Pulse measurement, Rating of per diode | 1.1                              |
| 反向峰值电流<br>Peak Reverse Current | $I_{RRM}$        | $\mu\text{A}$               | $V_{RM}=V_{RRM}$ , 脉冲测试, 单个二极管的额定值<br>$V_{RM}=V_{RRM}$ , Pulse measurement, Rating of per diode         | $T_j=25^{\circ}\text{C}$<br>5    |
|                                |                  |                             |                                                                                                         | $T_j=125^{\circ}\text{C}$<br>500 |
| 热阻<br>Thermal Resistance       | $R_{\theta J-A}$ | $^{\circ}\text{C}/\text{W}$ | 结和环境之间<br>Between junction and ambient                                                                  | 55                               |
|                                | $R_{\theta J-L}$ |                             | 结和引线之间<br>Between junction and lead                                                                     | 15                               |
|                                | $R_{\theta J-C}$ |                             | 结和壳之间<br>Between junction and case                                                                      | 10                               |

# ■特性曲线（典型） Characteristics(Typical)

图1:  $I_o$ - $T_c$  曲线  
FIG1:  $I_o$ - $T_c$  Curve

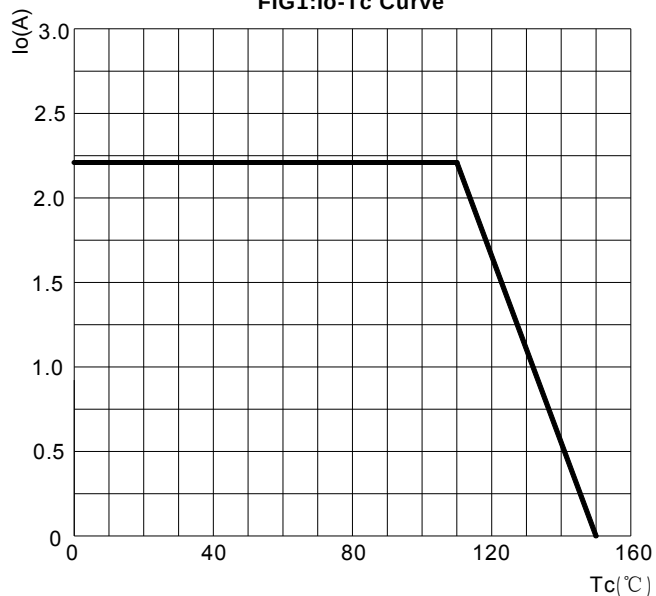


图2: 耐正向浪涌电流曲线  
FIG2: Surge Forward Current Capability

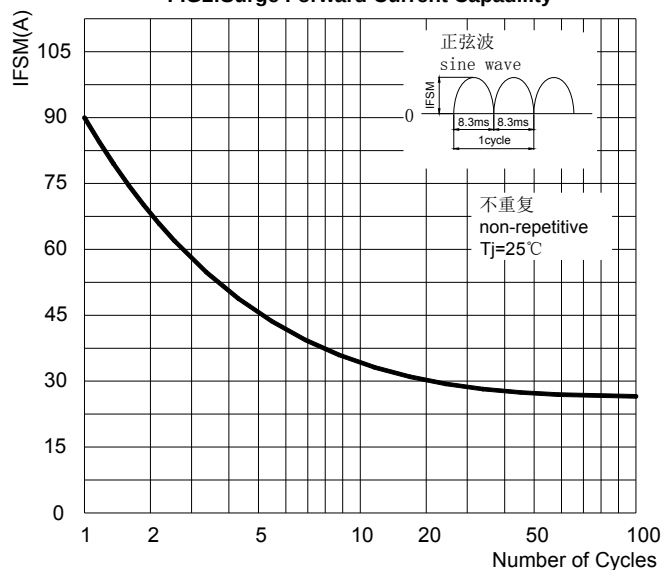


图3: 正向电压曲线  
FIG3: Forward Voltage

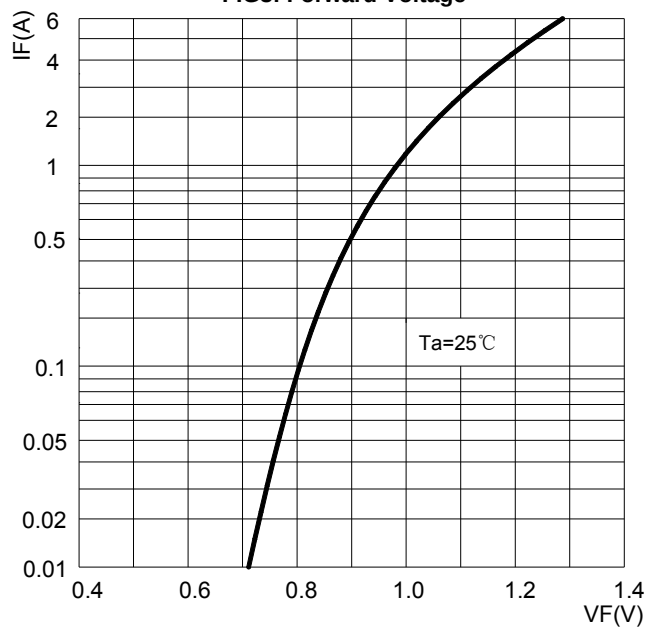


图4: 反向电流曲线  
FIG4: Typical Reverse Characteristics

